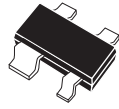


BAW100
BAW100G

**SURFACE MOUNT
DUAL, ISOLATED HIGH SPEED
SILICON SWITCHING DIODES**



SOT-143 CASE

CentralTM Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAW100 and BAW100G each consist of two electrically isolated high speed silicon switching diodes packaged in an epoxy molded SOT-143 surface mount case. This device is designed for high speed switching applications.

- The BAW100G is **Halogen Free** by design.

MARKING CODES:

BAW100: CJSS
BAW100G: CJSG

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Forward Surge Current, tp=1ms
Forward Surge Current, tp=1ms
Forward Surge Current, tp=1s
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V _R	75
V _R RM	85
I _F	250
I _{FRM}	500
I _{FSM}	4.0
I _{FSM}	2.0
I _{FSM}	1.0
P _D	350
T _J , T _{stg}	-65 to +150
Θ _{JA}	357

UNITS

V
V
mA
mA
A
A
A
mW
°C
°C/W

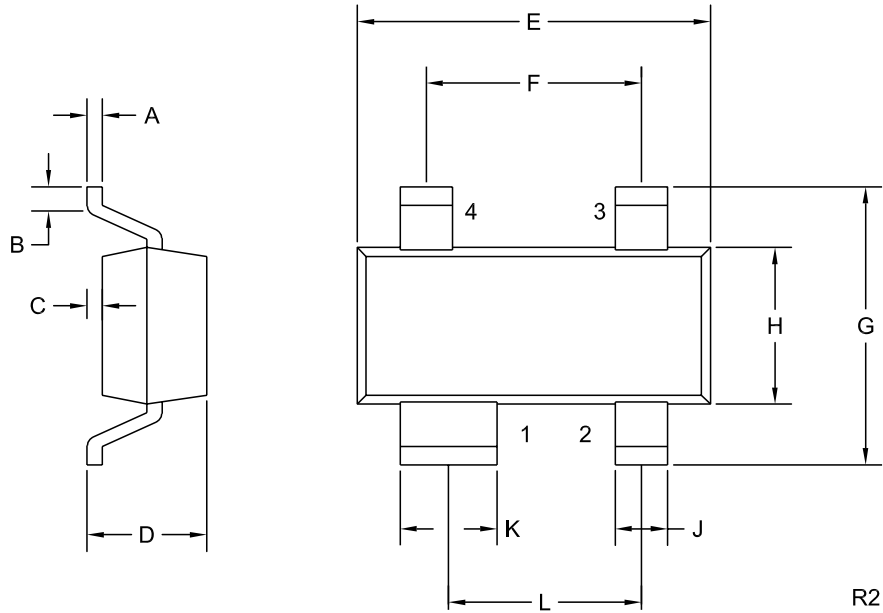
ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =25V, T _A =150°C		30	μA
I _R	V _R =75V		1.0	μA
I _R	V _R =75V, T _A =150°C		50	μA
BV _R	I _R =100μA	85		V
V _F	I _F =1.0mA		715	mV
V _F	I _F =10mA		855	mV
V _F	I _F =50mA		1.00	V
V _F	I _F =150mA		1.25	V
C _T	V _R =0, f=1.0 MHz		2.0	pF
t _{rr}	I _F =I _R =10mA, R _L =100Ω, Rec. to 1.0mA		6.0	ns

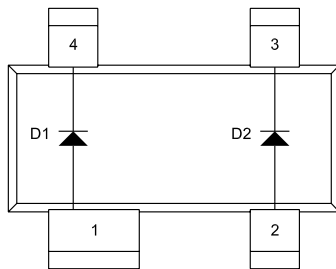
R3 (30-May 2008)

**SURFACE MOUNT
DUAL, ISOLATED HIGH SPEED
SILICON SWITCHING DIODES**

SOT-143 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) ANODE D1
- 2) ANODE D2
- 3) CATHODE D2
- 4) CATHODE D1

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075		1.90	
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067		1.70	

SOT-143 (REV: R2)

MARKING CODES:

- BAW100: CJSS
- BAW100G: CJSG